

EB13C3 J 2 H -25.000M

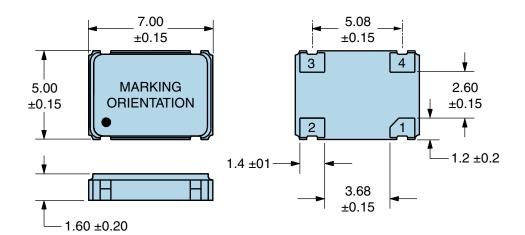
 Nominal Frequency 25.000MHz Logic Control / Additional Output Tri-State (High Impedance)

ELECTRICAL SPECIFICATIONS		
Nominal Frequency	25.000MHz	
Frequency Tolerance/Stability	±25ppm over -40°C to +85°C (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C, Shock, and Vibration)	
Supply Voltage	3.3Vdc ±10%	
Input Current	3mA Maximum	
Output Voltage Logic High (Voh)	90% of Vdd Minimum	
Input Current Logic High (Ioh)	-1.6mA	
Output Voltage Logic Low (Vol)	10% of Vdd Maximum	
Input Current Logic Low (IoI)	+1.6mA	
Rise/Fall Time	6nSec Maximum (Measured at 20% to 80% of waveform)	
Duty Cycle	50 ±5(%) (Measured at 50% of waveform)	
Load Drive Capability	15pF Maximum	
Output Logic Type	CMOS	
Logic Control / Additional Output	Tri-State (High Impedance)	
Tri-State Input Voltage (Vih and Vil)	90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)	
Standby Current	10μA Maximum (Disabled Output: High Impedance)	
One Sigma Clock Period Jitter	25pSec Maximum	
Start Up Time	10mSec Maximum	
Storage Temperature Range	-55°C to +125°C	

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS		
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-202, Method 213, Condition C	
Resistance to Soldering Heat	MIL-STD-202, Method 210	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010	
Vibration	MIL-STD-883, Method 2007, Condition A	



MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
2	Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	25.000M
3	XXYZZ XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year

Suggested Solder Pad Layout

All Dimensions in Millimeters



All Tolerances are ±0.1



OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



- Note 1: An external $0.1\mu\text{F}$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu\text{F}$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.
- Note 3: Capacitance value \dot{C}_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods

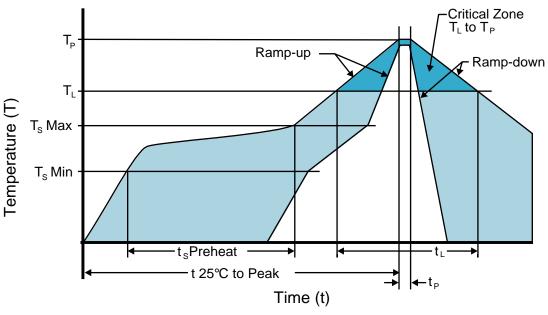


High Temperature Infrared/Convection

3°C/second Maximum
150°C
175°C
200°C
60 - 180 Seconds
3°C/second Maximum
217°C
60 - 150 Seconds
260°C Maximum for 10 Seconds Maximum
250°C +0/-5°C
20 - 40 seconds
6°C/second Maximum
8 minutes Maximum
Level 1
Temperatures shown are applied to body of device.



Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

T _s MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
- Temperature Typical (T _s TYP)	150°C
- Temperature Maximum (T _s MAX)	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T _L to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (tp)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)